# PF01411B

MOS FET Power Amplifier Module for E-GSM Handy Phone

# HITACHI

ADE-208-434B (Z) 3rd Edition Nov. 1997

#### **Application**

- For E-GSM class4 880 to 915 MHz
- For 3.5 V nominal battery use

#### **Features**

• High gain 3stage amplifier: 0 dBm input

• Lead less thin & Small package: 2 mm Max, 0.2cc

High efficiency: 45% Typ at 35.5 dBmWide gain control range: 70 dB Typ

#### **Pin Arrangement**



- 1: Pin
- 2: Vapc
- 3: Vdd
- 4: Pout
- G: GND

#### **Absolute Maximum Ratings** ( $Tc = 25^{\circ}C$ )

Item	Symbol	Rating	Unit
Supply voltage	$V_{DD}$	8	V
Supply current	I <sub>DD</sub>	3	A
V <sub>APC</sub> voltage	$V_{APC}$	4	V
Input power	Pin	10	mW
Operating case temperature	Tc (op)	-30 to +100	°C
Storage temperature	Tstg	-30 to +100	°C
Output power	Pout	5	W



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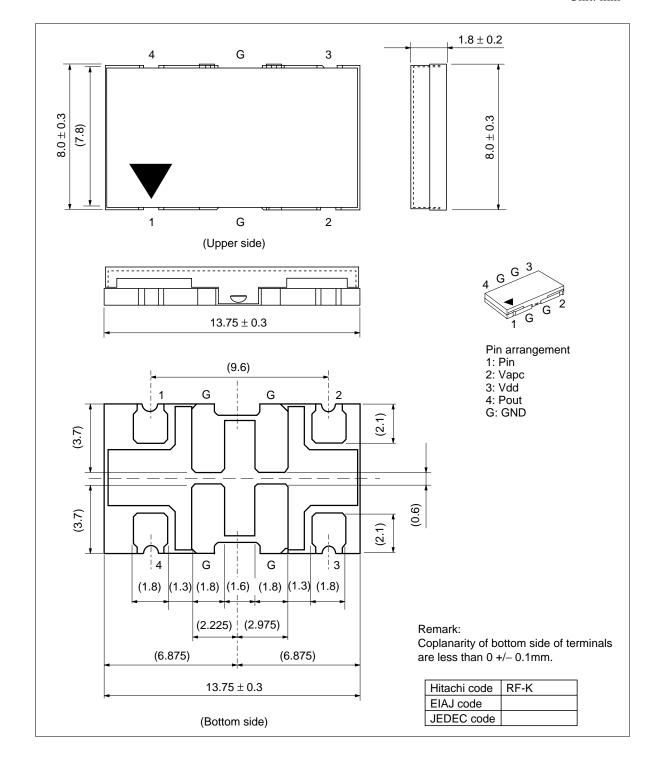
### **Electrical Characteristics** ( $Tc = 25^{\circ}C$ )

Item	Symbol	Min	Тур	Max	Unit	Test Condition
Frequency range	f	880	_	915	MHz	
Control voltage range	$V_{\mathtt{APC}}$	0.5	_	2.2	V	
Drain cutoff current	I <sub>DS</sub>	_	_	100	μΑ	$V_{DD} = 8V, V_{APC} = 0V$
Total efficiency	$\eta_{\scriptscriptstyle \sf T}$	40	45	_	%	$Pin = 0dBm, V_{DD} = 3.5V,$
2nd harmonic distortion	2nd H.D.	_	-45	-35	dBc	Pout = 35.5dBm, Vapc = control
3rd harmonic distortion	3rd H.D.	_	-45	-35	dBc	$R_L = Rg = 50\Omega$ , $Tc = 25^{\circ}C$
Input VSWR	VSWR (in)	_	1.5	3	_	-
Output power (1)	Pout (1)	35.5	36.0	_	dBm	$Pin = 0dBm, V_{DD} = 3.5V,$ $V_{APC} = 2.2V, R_{L} = Rg = 50Ω,$ $Tc = 25^{\circ}C$
Output power (2)	Pout (2)	33.5	34.2	_	dBm	$\begin{aligned} &\text{Pin} = \text{0dBm, V}_{\text{DD}} = 3.0\text{V,} \\ &\text{V}_{\text{APC}} = 2.2\text{V, R}_{\text{L}} = \text{Rg} = 50\Omega, \\ &\text{Tc} = 85^{\circ}\text{C} \end{aligned}$
Isolation	_	_	-40	-36	dBm	Pin = 0dBm, $V_{DD}$ = 3.5V, $V_{APC}$ = 0.5V, $R_{L}$ = Rg = 50Ω, Tc = 25°C
Switching time	tr, tf	_	1	2	μs	Pin = 0dBm, $V_{DD} = 3.5V$ , Pout = 0 to 35.5dBm $R_L = Rg = 50\Omega$ , $Tc = 25^{\circ}C$
Stability	_	No parasitic oscillation			_	Pin = 0dBm, $V_{DD}$ = 3 to 5.1V, Pout $\leq$ 35.5dBm, Vapc $\leq$ 2.2V GSM pulse. Rg = 50 $\Omega$ , Tc = 25°C, Output VSWR = 6 : 1 All phases
Load VSWR tolerance	_	No degradation				Pin = 0dBm, $V_{DD}$ = 3 to 5.1V, Pout $\leq$ 35.5dBm, Vapc $\leq$ 2.2V GSM pulse. Rg = $50\Omega$ , t = $20$ sec., Tc = $25$ °C, Output VSWR = $10$ : 1 All phases

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### **Package Dimensions**

Unit: mm



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